

isc N-Channel MOSFET Transistor

2SK958

DESCRIPTION

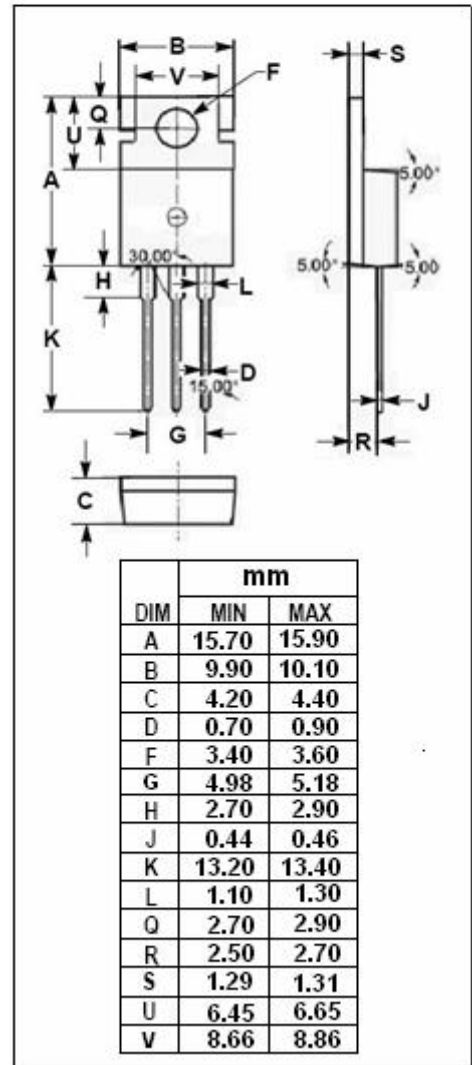
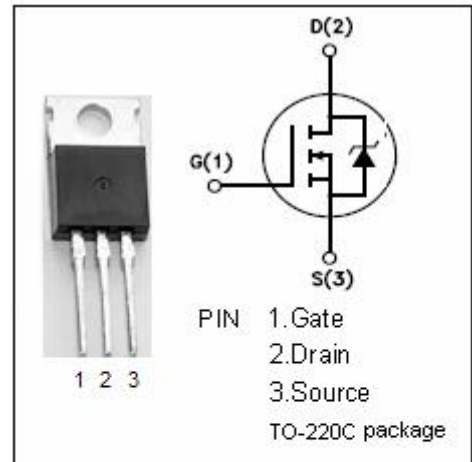
- Drain Current  $-I_D=2A @ T_C=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS}=900V(\text{Min})$

APPLICATIONS

- Designed especially for high voltage.
- high speed power switching.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	900	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-continuous@ $T_C=25^\circ C$	2	A
$P_{tot}$	Total Dissipation@ $T_C=25^\circ C$	45	W
$T_j$	Max. Operating Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc N-Channel MOSFET Transistor****2SK958****• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
(BR)DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0; I <sub>D</sub> = 1mA	900			V
V <sub>GS(TH)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 1mA	2.5	3.5	5.0	V
R <sub>DS(ON)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =1A			8.5	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±20V; V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =900V; V <sub>GS</sub> = 0			500	uA